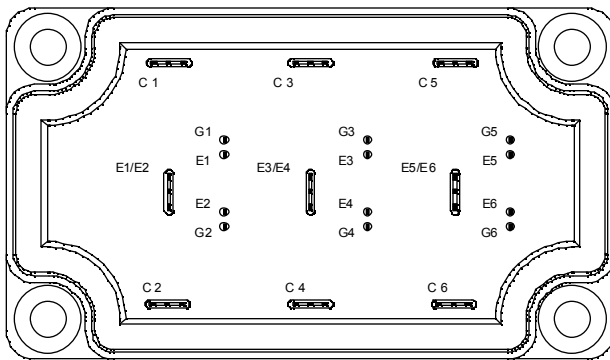
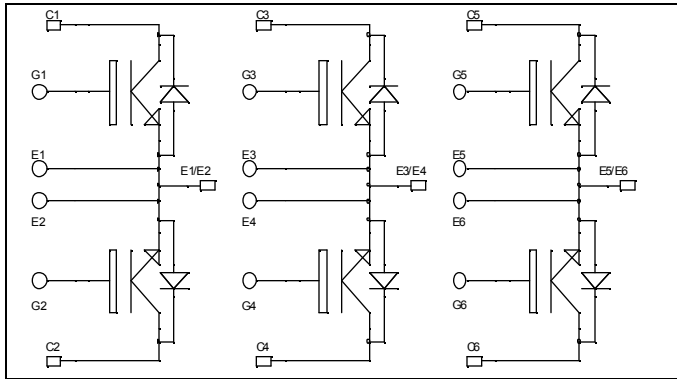


Triple Dual Common Source Trench IGBT® Power Module

$$V_{CES} = 1700V$$

$$I_C = 50A @ T_c = 80^{\circ}C$$



Application

- AC Switches
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- Trench + Field Stop IGBT® Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - Avalanche energy rated
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- High level of integration
- Kelvin emitter for easy drive

Benefits

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Very low (12mm) profile
- Each leg can be easily paralleled to achieve a dual common source configuration of three times the current capability

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage	1700	V
I_C	Continuous Collector Current	$T_C = 25^{\circ}C$	A
		$T_C = 80^{\circ}C$	
I_{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	100
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Maximum Power Dissipation	$T_C = 25^{\circ}C$	310
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^{\circ}C$	100A @ 1600V

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
BV_{CES}	Collector - Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 2.5mA$	1700			V
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1700V$			5	mA
$V_{CE(on)}$	Collector Emitter on Voltage	$V_{GE} = 15V$ $I_C = 50A$		$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	2.0 2.4	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 2.5mA$	5.0		6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$			600	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0V, V_{CE} = 25V$		4400		pF
C_{rss}	Reverse Transfer Capacitance	$f = 1MHz$		150		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = \pm 15V$ $V_{Bus} = 900V$ $I_C = 50A$ $R_G = 22\Omega$		200		ns
T_r	Rise Time			90		
$T_{d(off)}$	Turn-off Delay Time			720		
T_f	Fall Time			90		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) $V_{GE} = \pm 15V$ $V_{Bus} = 900V$ $I_C = 50A$ $R_G = 22\Omega$ Diode		220		ns
T_r	Rise Time			90		
$T_{d(off)}$	Turn-off Delay Time			820		
T_f	Fall Time			110		
E_{on}	Turn-on Switching Energy ❶			29		mJ
E_{off}	Turn-off Switching Energy ❷			22		

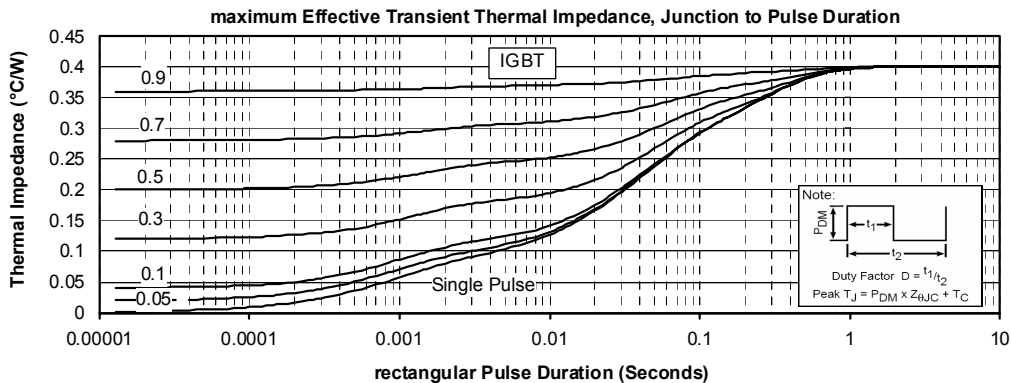
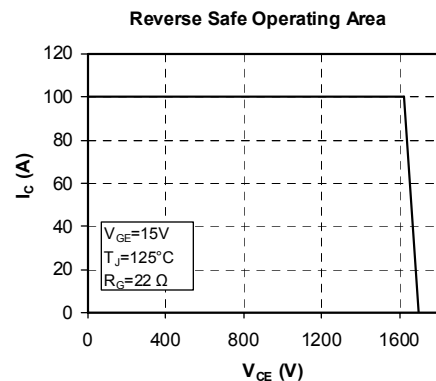
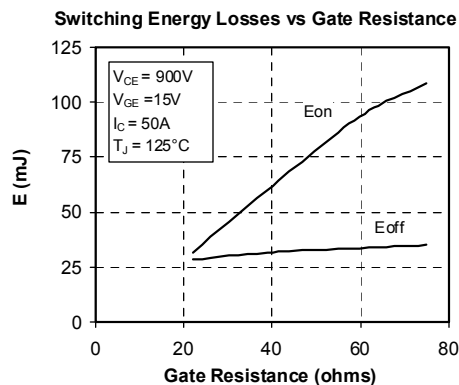
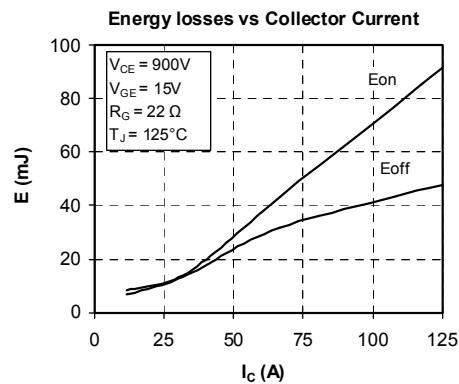
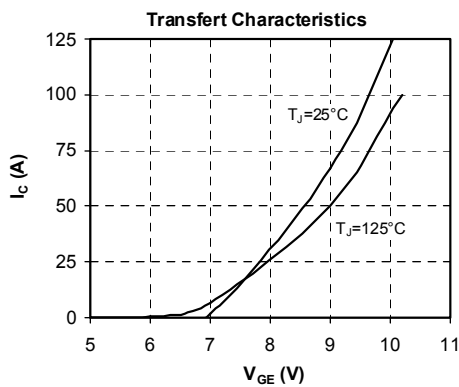
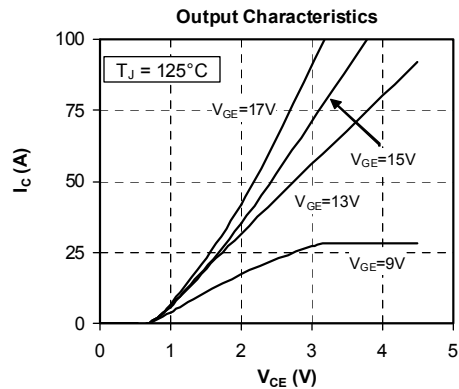
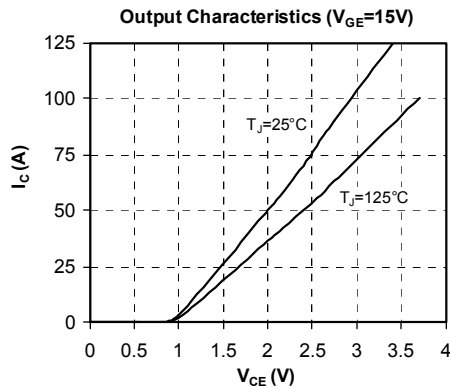
❶ E_{on} includes diode reverse recovery

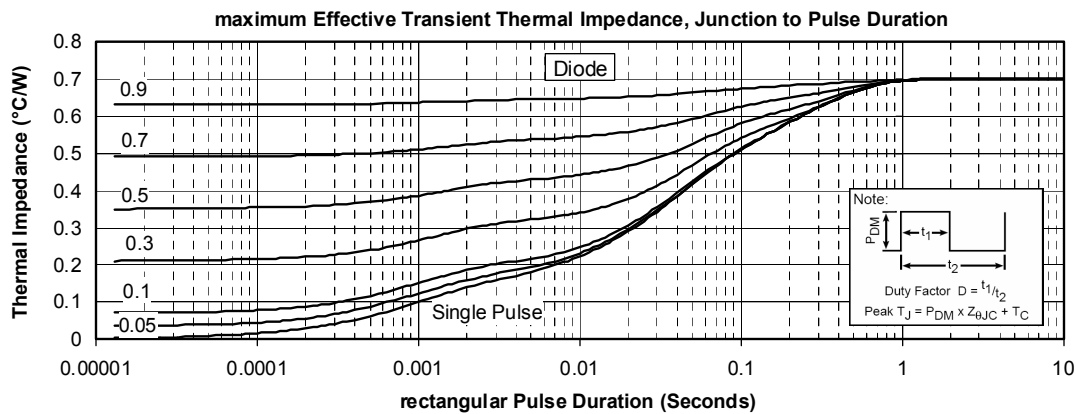
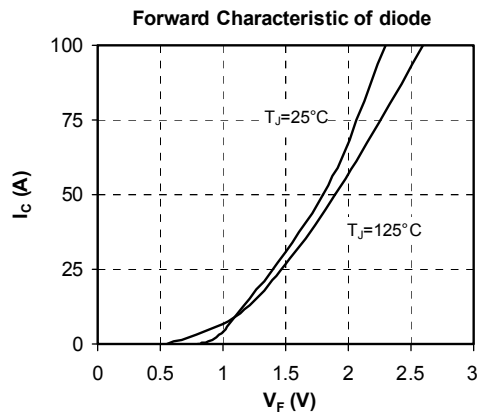
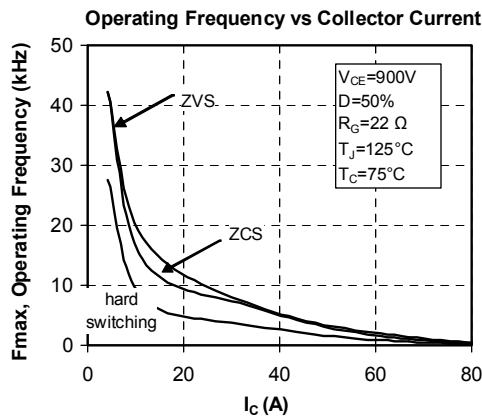
❷ In accordance with JEDEC standard JESD24-1

Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		1700			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 1700V$			$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	μA
V_F	Diode Forward Voltage	$I_F = 50A$ $V_{GE} = 0V$		$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	1.8 1.9	V
Q_{rr}	Reverse Recovery Charge	$I_F = 50A$ $V_R = 900V$ $di/dt = 990A/\mu s$		$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	19 30	μC

Typical Performance Curve





APT reserves the right to change, without notice, the specifications and information contained herein

APT's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S and Foreign patents pending. All Rights Reserved.